			DB	Time stamp
Number	Hits	Search Text gate near electrode\$1 and polysilicon	USPAT;	2003/07/21 10:38
	26372	gate near electrodest and polysizzon	US-PGPUB;	
			EPO; JPO;	
			DERWENT	2003/07/02 10:47
	25	(gate near electrode\$1 and polysilicon)	USPAT;	2003/07/02 10:47
		and polish\$3 near5 silicide	US-PGPUB; EPO; JPO;	
			DERWENT	
Ì			USPAT	2003/07/02 10:25
- i	11	("5683941" "5770507" "5817562" "5824588" "5904533" "5953614"	002111	
		5024500 1 100131 100131601		
		"5985768" "6001721" "6013369 "6072222" "6074921" "9084280").PN.		
	32	("4514233" "4577392" "4616401"	USPAT	2003/07/02 10:30
-	32	"4803173" "4826781" "4829025"		
		"4935376" "4948745" "4992388"	'	
		"5045483" "5168072" "5268330"		
		"5306665" "5310692" "5366911"		
		"5391510" "5411909" "5429987" "5434093" "5447875" "5496771"		
		5454055 STATE OF 661 !!		
		"5516716" "5545579" "5585661 "5610083" "5633187" "5656519"		
		"5683941" "5731239" "5780349"		
		"5843834" "5953612").PN.		2003/07/02 10:32
_	17	("4514233" "4803173" "4935376"	USPAT	2003/01/02 10.32
		"5268330" "5310692" "5366911"		
	i l	"5411909" "5434093" "5447875"		
		"5496771" "5516716" "5545579" "5585661" "5610083" "5633187"		
		3363001 33210024H) PM		
	18	"5683941" "5843834").FN. ("4518629" "4587718" "4690730"	USPAT	2003/07/02 10:35
_	10	"4740484" "4746219" "4753709"		
		"4755478" "4795722" "4824521"		
		"4849369" "4877775" "4966870"		
		"4994402" "5013678" "5022958"		
		"5034348" "5081065" "5086017").PN.	USPAT	2003/07/02 10:35
_	11	("4545116" "4575920" "4622735" "4755478" "4795722" "4822754"	001711	
		4755470 1 11403330711 1		
		"4859278" "4914500" "4933297 "4965226" "5023204").PN.		105 100 10 15
	12	("4807007" "4984042" "5200352"	USPAT	2003/07/02 10:45
-	12	"5391510" "5532181" "5668035"		
		"5904508" "6033958" "6037201"		
			1 5000000000000000000000000000000000000	152003/07/02 10:48
-	8085	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	US-PGPUB;	101000,01,02 2011
			EPO; JPO;	
			DERWENT	
	2107	438/299,592,301,305,306,307,595,706,720,72	1,69PA693.cc	1s2003/07/02 10:45
-	3107	and gate near electrode\$1	US-PGPUB;	
		and gate near section.	EPO; JPO;	
			DERWENT	12003/07/02 10.4
_	9	(438/299, 592, 301, 305, 306, 307, 595, 706, 720, 7	US-PGPUB;	CL2003/01/02 10.4
		and gate near electrode\$1) and polishas	EPO; JPO;	
1		near5 silicide\$1	DERWENT	
		polish\$3 near3 rate same dish\$3	USPAT;	2003/07/21 10:4
_	453	polisnos nears race same dismos	US-PGPUB;	
			EPO; JPO;	
			DERWENT	0000/07/01 10 4
_	422	(polish\$3 near3 rate same dish\$3) and	USPAT;	2003/07/21 10:4
	122	semiconductor	US-PGPUB;	
			EPO; JPO;	
			DERWENT D USPAT;	2003/07/21 10:4
-	40	polish\$3 near3 rate same etch\$3 near2 sto	US-PGPUB;	
			EPO; JPO;	
1	1	· I	DERWENT	1

_ 38	(polish\$3 near3 rate same etch\$3 near2 stop) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/07/21 10:48	

Search History 7/21/03 1:22:37 PM Page 2